

# NXH80B120H2Q0

## Q0 - Dual Boost Power Module

The NXH80B120H2Q0 is a high-density, integrated power module combines high-performance IGBTs with rugged anti-parallel diodes including on-board thermistor.

### Features

- Dual Boost 40 A / 1200 V IGBT + SiC Rectifier Hybrid Module
- 1200 V FSII IGBT  $V_{CE(SAT)} = 2.2\text{ V}$
- 1200 V SiC Diode  $V_F = 1.4\text{ V}$
- Low Inductive Layout
- Solderable Pins
- Thermistor
- Bare Copper and Nickel-Plated DBC Options

### Typical Applications

- Solar Inverter
- Uninterruptible Power Supplies
- Energy Storage Systems

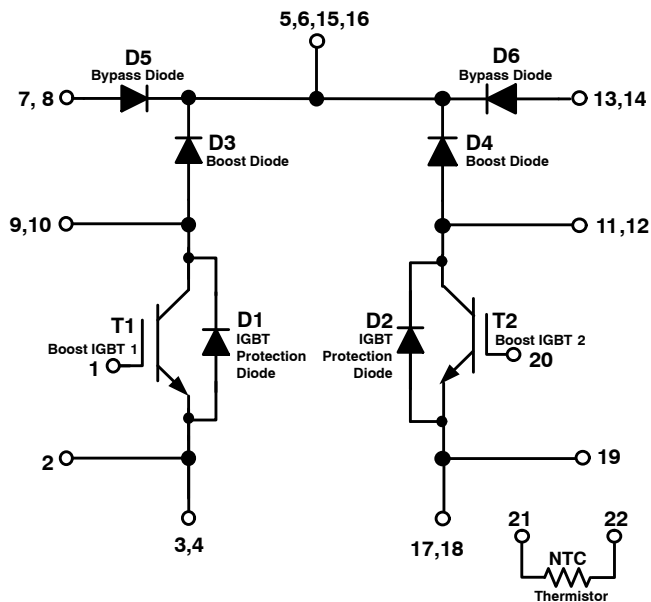
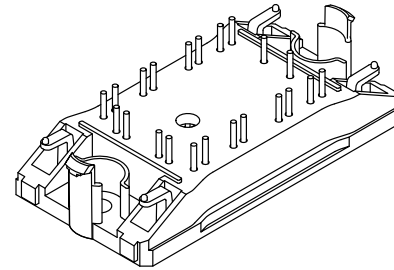


Figure 1. NXH80B120H2Q0SG Schematic Diagram



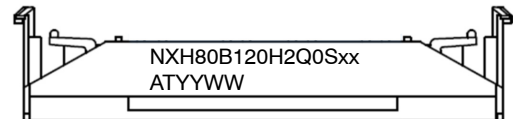
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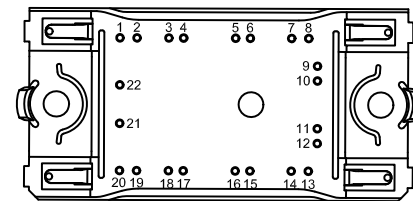
**Q0BOOST  
CASE 180AJ**

### MARKING DIAGRAM



NXH80B120H2Q0Sxx = Device Code  
AT = Assembly & Test Site Code  
YYWW = Year and Work Week Code

### PIN CONNECTIONS



### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 4 of this data sheet.

# NXH80B120H2Q0

**Table 1. ABSOLUTE MAXIMUM RATINGS** (Note 1)  $T_J = 25^\circ\text{C}$  unless otherwise noted

Rating	Symbol	Value	Unit
<b>BOOST IGBT</b>			
Collector-Emitter Voltage	$V_{CES}$	1200	V
Gate-Emitter Voltage	$V_{GE}$	$\pm 20$	V
Continuous Collector Current @ $T_h = 80^\circ\text{C}$ ( $T_J = 175^\circ\text{C}$ )	$I_C$	41	A
Pulsed Collector Current ( $T_J = 175^\circ\text{C}$ )	$I_{Cpulse}$	123	A
Maximum Power Dissipation @ $T_h = 80^\circ\text{C}$ ( $T_J = 175^\circ\text{C}$ )	$P_{tot}$	103	W
Short Circuit Withstand Time @ $V_{GE} = 15\text{ V}$ , $V_{CE} = 600\text{ V}$ , $T_J \leq 150^\circ\text{C}$	$T_{sc}$	5	$\mu\text{s}$
Minimum Operating Junction Temperature	$T_{JMIN}$	-40	$^\circ\text{C}$
Maximum Operating Junction Temperature	$T_{JMAX}$	150	$^\circ\text{C}$

<b>BOOST DIODE</b>			
Peak Repetitive Reverse Voltage	$V_{RRM}$	1200	V
Continuous Forward Current @ $T_h = 80^\circ\text{C}$ ( $T_J = 175^\circ\text{C}$ )	$I_F$	28	A
Repetitive Peak Forward Current (limited by $T_J$ , duty cycle = 10%)	$I_{FRM}$	75	A
Maximum Power Dissipation @ $T_h = 80^\circ\text{C}$ ( $T_J = 175^\circ\text{C}$ )	$P_{tot}$	79	W
Surge Forward Current (60 Hz single half-sine wave) ( $T_J = 25^\circ\text{C}$ )	$I_{FSM}$	69	A
$I^2t$ - value (60 Hz single half-sine wave) ( $T_J = 150^\circ\text{C}$ )	$I^2t$	19	$\text{A}^2\text{s}$
Minimum Operating Junction Temperature	$T_{JMIN}$	-40	$^\circ\text{C}$
Maximum Operating Junction Temperature	$T_{JMAX}$	150	$^\circ\text{C}$

<b>BYPASS DIODE / IGBT PROTECTION DIODE</b>			
Peak Repetitive Reverse Voltage	$V_{RRM}$	1600	V
Continuous Forward Current @ $T_h = 80^\circ\text{C}$ ( $T_J = 175^\circ\text{C}$ )	$I_F$	46	A
Repetitive Peak Forward Current ( $T_J = 175^\circ\text{C}$ , $t_p$ limited by $T_{Jmax}$ )	$I_{FRM}$	130	A
Power Dissipation Per Diode @ $T_h = 80^\circ\text{C}$ ( $T_J = 175^\circ\text{C}$ )	$P_{tot}$	66	W
Minimum Operating Junction Temperature	$T_{JMIN}$	-40	$^\circ\text{C}$
Maximum Operating Junction Temperature	$T_{JMAX}$	150	$^\circ\text{C}$

### THERMAL PROPERTIES

Storage Temperature range	$T_{stg}$	-40 to 125	$^\circ\text{C}$
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### INSULATION PROPERTIES

Isolation test voltage, $t = 1\text{ sec}$ , 60 Hz	$V_{is}$	3000	$V_{RMS}$
Creepage distance		12.7	mm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.

**Table 2. RECOMMENDED OPERATING RANGES**

Rating	Symbol	Min	Max	Unit
Module Operating Junction Temperature	$T_J$	-40	( $T_{jmax} - 25$ )	$^\circ\text{C}$

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

# NXH80B120H2Q0

**Table 3. ELECTRICAL CHARACTERISTICS**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
<b>BOOST IGBT CHARACTERISTICS</b>						
Collector-Emitter Cutoff Current	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$	$I_{CES}$	–	–	200	$\mu\text{A}$
Collector-Emitter Saturation Voltage	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 25^\circ\text{C}$	$V_{CE(sat)}$	–	2.20	2.5	V
	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 150^\circ\text{C}$		–	2.16	–	
Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5\text{ mA}$	$V_{GE(TH)}$	–	5.45	6.4	V
Gate Leakage Current	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	$I_{GES}$	–	–	200	nA
Turn-on Delay Time	$T_J = 25^\circ\text{C}$ $V_{CE} = 700\text{ V}, I_C = 40\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4\ \Omega$	$t_{d(on)}$	–	27	–	ns
Rise Time		$t_r$	–	19	–	
Turn-off Delay Time		$t_{d(off)}$	–	94	–	
Fall Time		$t_f$	–	78	–	
Turn-on Switching Loss per Pulse		$E_{on}$	–	540	–	
Turn-off Switching Loss per Pulse	$E_{off}$	–	1640	–		
Turn-on Delay Time	$T_J = 125^\circ\text{C}$ $V_{CE} = 700\text{ V}, I_C = 40\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4\ \Omega$	$t_{d(on)}$	–	27	–	ns
Rise Time		$t_r$	–	20	–	
Turn-off Delay Time		$t_{d(off)}$	–	110	–	
Fall Time		$t_f$	–	189	–	
Turn-on Switching Loss per Pulse		$E_{on}$	–	620	–	
Turn-off Switching Loss per Pulse	$E_{off}$	–	3590	–		
Input Capacitance	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 10\text{ kHz}$	$C_{ies}$	–	9700	–	pF
Output Capacitance		$C_{oes}$	–	200	–	
Reverse Transfer Capacitance		$C_{res}$	–	170	–	
Total Gate Charge	$V_{CE} = 600\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}$	$Q_g$	–	400	–	nC
Thermal Resistance – chip-to-heatsink	Thermal grease, Thickness < 100 $\mu\text{m}$ , $\lambda = 0.84\text{ W/mK}$	$R_{thJH}$	–	0.92	–	$^\circ\text{C/W}$

### BOOST DIODE CHARACTERISTICS

Diode Reverse Leakage Current	$V_R = 1200\text{ V}$	$I_R$	–	–	300	$\mu\text{A}$
Diode Forward Voltage	$I_F = 15\text{ A}, T_J = 25^\circ\text{C}$	$V_F$	–	1.42	1.7	V
	$I_F = 15\text{ A}, T_J = 150^\circ\text{C}$		–	1.95	–	
Reverse Recovery Time	$T_J = 25^\circ\text{C}$ $V_{CE} = 700\text{ V}, I_C = 40\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4\ \Omega$	$t_{rr}$	–	27	–	ns
Reverse Recovery Charge		$Q_{rr}$	–	280	–	nC
Peak Reverse Recovery Current		$I_{RRM}$	–	16	–	A
Peak Rate of Fall of Recovery Current		$di/dt$	–	1080	–	$\text{A}/\mu\text{s}$
Reverse Recovery Energy		$E_{rr}$	–	130	–	$\mu\text{J}$
Reverse Recovery Time	$T_J = 125^\circ\text{C}$ $V_{CE} = 700\text{ V}, I_C = 40\text{ A}$ $V_{GE} = \pm 15\text{ V}, R_G = 4\ \Omega$	$t_{rr}$	–	28	–	ns
Reverse Recovery Charge		$Q_{rr}$	–	250	–	nC
Peak Reverse Recovery Current		$I_{RRM}$	–	15	–	A
Peak Rate of Fall of Recovery Current		$di/dt$	–	940	–	$\text{A}/\mu\text{s}$
Reverse Recovery Energy		$E_{rr}$	–	110	–	$\mu\text{J}$
Thermal Resistance – chip-to-heatsink	Thermal grease, Thickness < 100 $\mu\text{m}$ , $\lambda = 0.84\text{ W/mK}$	$R_{thJH}$	–	1.21	–	$^\circ\text{C/W}$

### BYPASS DIODE/IGBT PROTECTION DIODE CHARACTERISTICS

Diode Reverse Leakage Current	$V_R = 1600\text{ V}, T_J = 25^\circ\text{C}$	$I_R$	–	–	100	$\mu\text{A}$
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# NXH80B120H2Q0

**Table 3. ELECTRICAL CHARACTERISTICS**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
<b>BYPASS DIODE/IGBT PROTECTION DIODE CHARACTERISTICS</b>						
Diode Forward Voltage	$I_F = 25\text{ A}, T_J = 25^\circ\text{C}$	$V_F$	–	1.0	1.4	V
	$I_F = 25\text{ A}, T_J = 150^\circ\text{C}$		–	0.90	–	
Thermal Resistance – chip-to-heatsink	Thermal grease, Thickness < 100 $\mu\text{m}$ , $\lambda = 0.84\text{ W/mK}$	$R_{thJH}$	–	1.44	–	$^\circ\text{C/W}$

### THERMISTOR CHARACTERISTICS

Nominal resistance		$R_{25}$	–	22	–	$\text{k}\Omega$
Nominal resistance	$T = 100^\circ\text{C}$	$R_{100}$	–	1486	–	$\Omega$
Deviation of R25		$\Delta R/R$	–5	–	5	%
Power dissipation		$P_D$	–	200	–	mW
Power dissipation constant			–	2	–	mW/K
B-value	B(25/50), tolerance $\pm 3\%$		–	3950	–	K
B-value	B(25/100), tolerance $\pm 3\%$		–	3998	–	K

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### ORDERING INFORMATION

Orderable Part Number	Marking	Package	Shipping
NXH80B120H2Q0SG	NXH80B120H2Q0SG	Q0BOOST – Case 180AJ Bare Copper DBC, Solder Pins (Pb-Free and Halide-Free)	24 Units / Blister Tray
NXH80B120H2Q0SNG	NXH80B120H2Q0SNG	Q0BOOST – Case 180AJ Nickel-Plated DBC, Solder Pins (Pb-Free and Halide-Free)	24 Units / Blister Tray

# NXH80B120H2Q0

## TYPICAL CHARACTERISTICS – Boost IGBT & Boost Diode

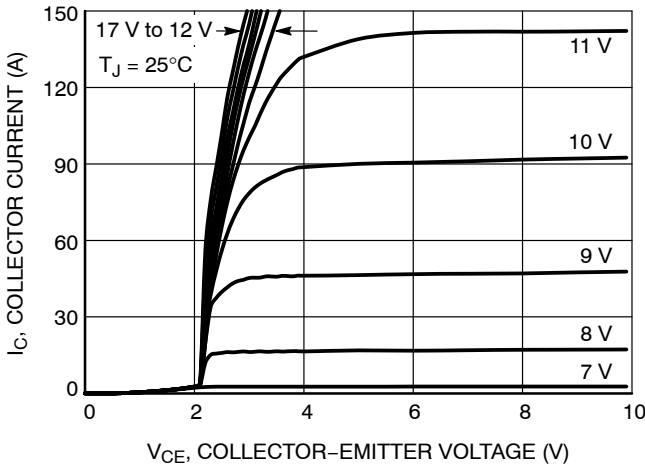


Figure 1. IGBT Typical Output Characteristics

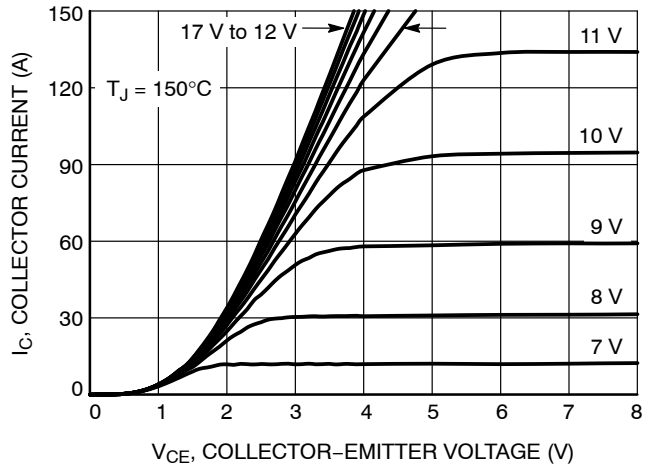


Figure 2. IGBT Typical Output Characteristics

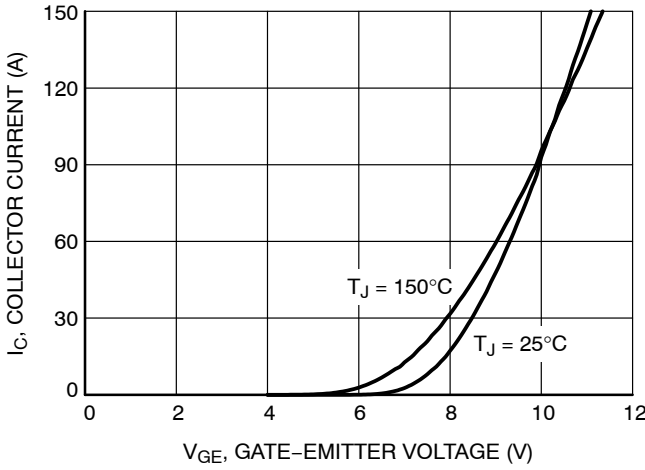


Figure 3. IGBT Typical Transfer Characteristics

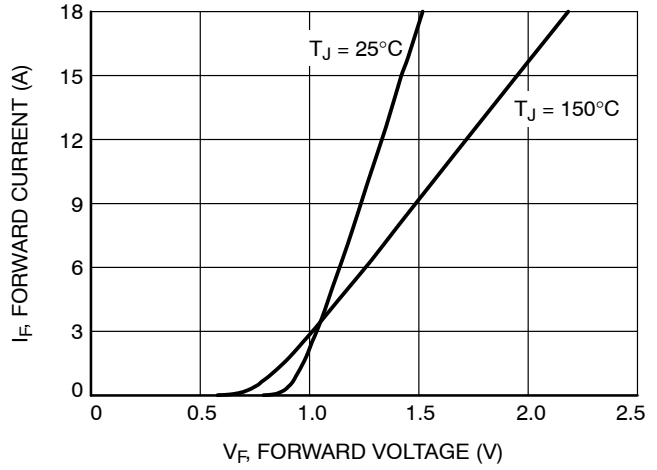


Figure 4. Diode Forward Characteristic

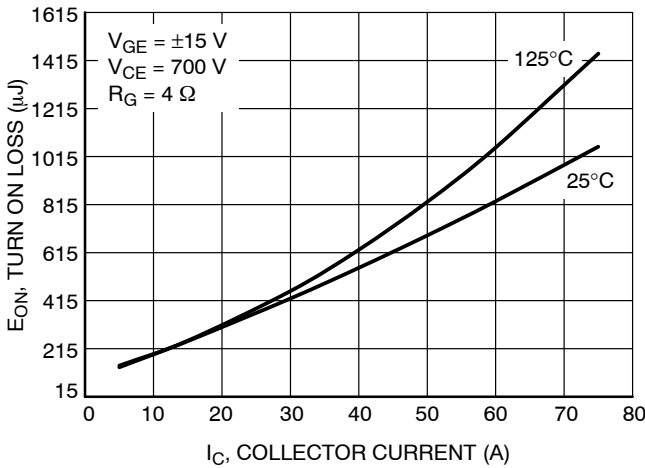


Figure 5. Typical Turn On Loss vs. Ic

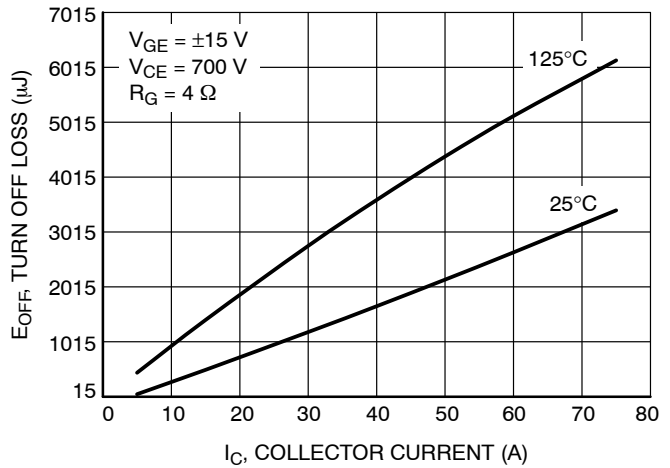


Figure 6. Typical Turn Off Loss vs. Ic

# NXH80B120H2Q0

## TYPICAL CHARACTERISTICS – Boost IGBT & Boost Diode

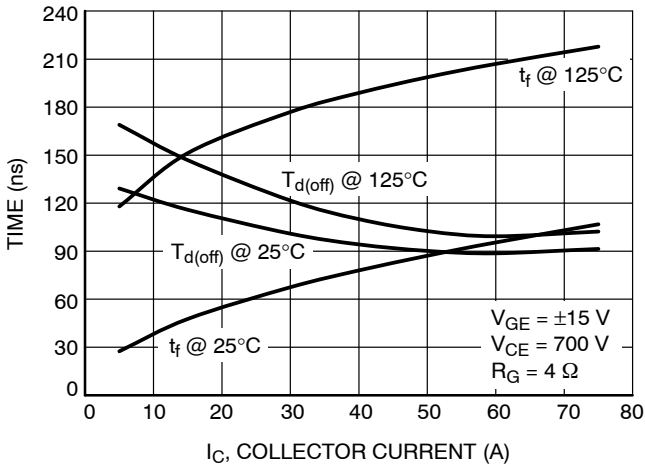


Figure 7. Typical Switching Times vs.  $I_C$

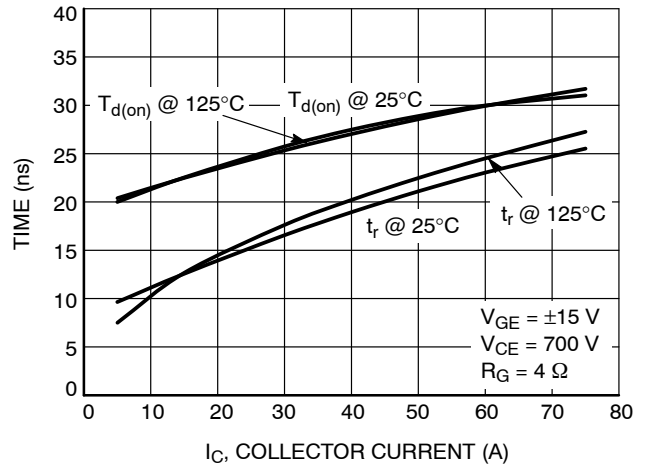


Figure 8. Typical Switching Times vs.  $I_C$

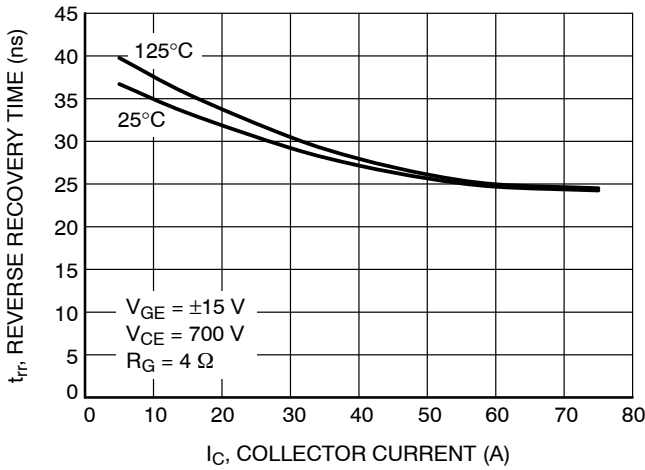


Figure 9. Typical Reverse Recovery Time vs.  $I_C$

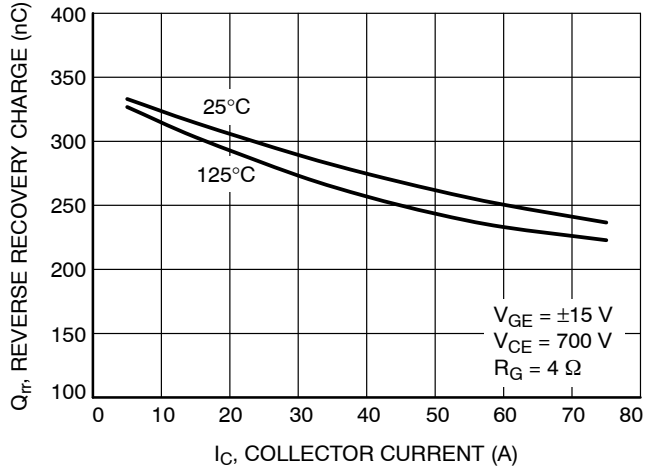


Figure 10. Typical Reverse Recovery Charge vs.  $I_C$

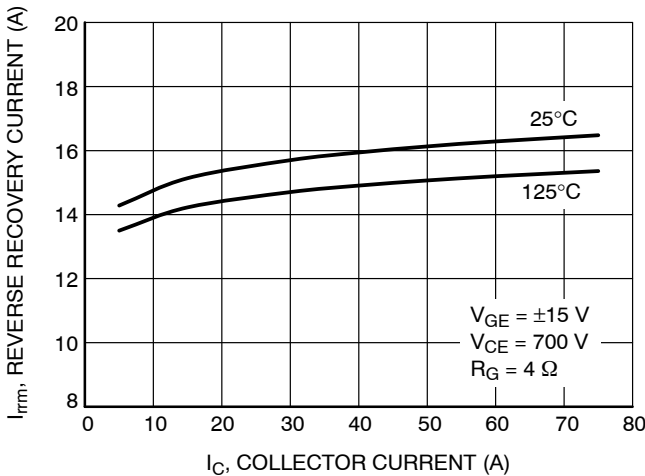


Figure 11. Typical Reverse Recovery Peak Current vs.  $I_C$

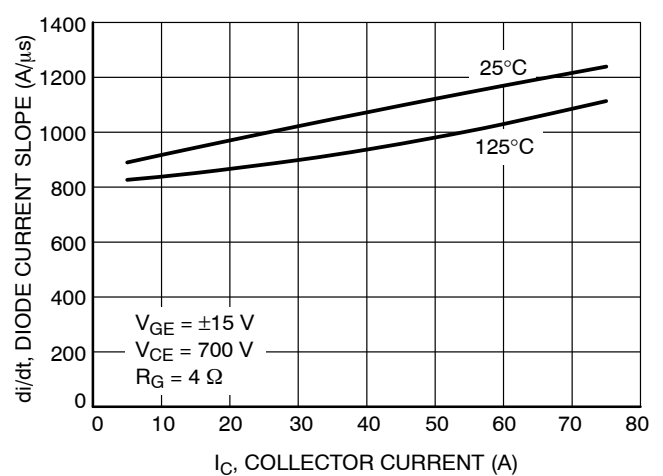


Figure 12. Typical Diode Current Slope vs.  $I_C$

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## TYPICAL CHARACTERISTICS – Boost IGBT & Boost Diode

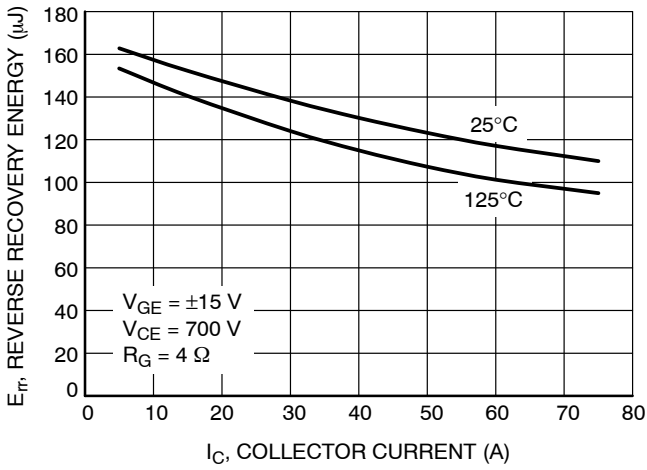


Figure 13. Typical Reverse Recovery Energy vs.  $I_C$

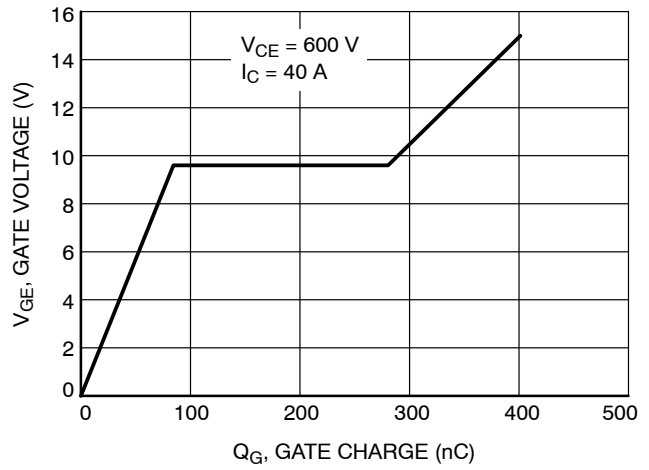


Figure 14. Gate Voltage vs. Gate Charge

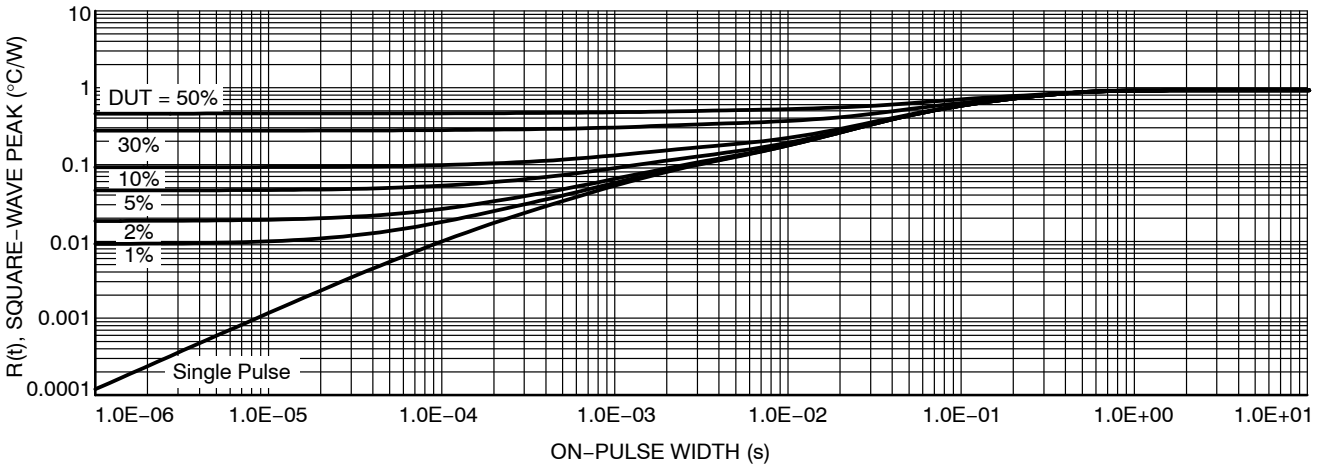


Figure 15. IGBT Transient Thermal Impedance

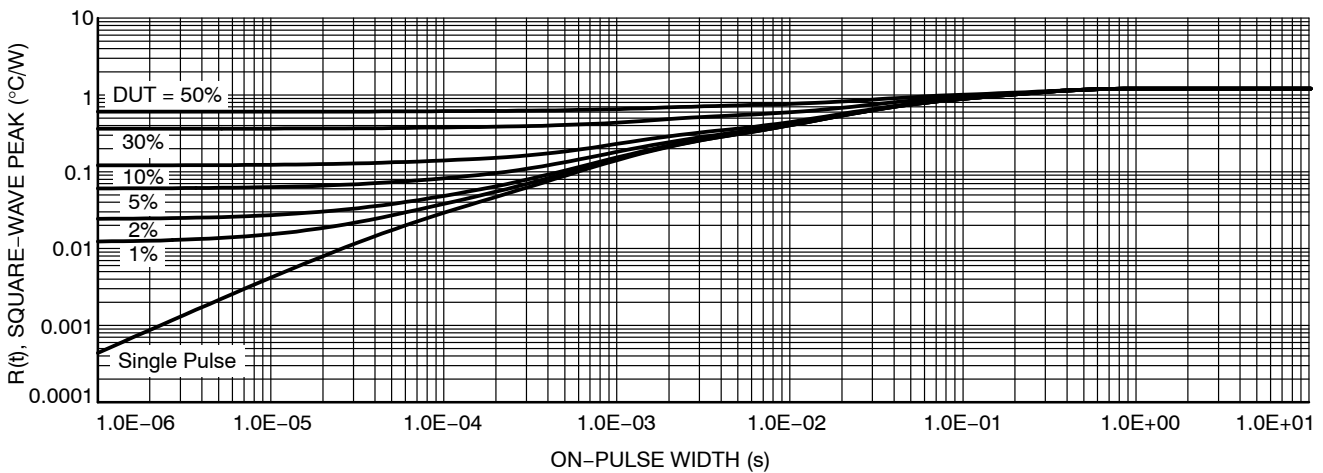


Figure 16. Diode Transient Thermal Impedance Boost Diode

# NXH80B120H2Q0

## TYPICAL CHARACTERISTICS – Boost IGBT & Boost Diode

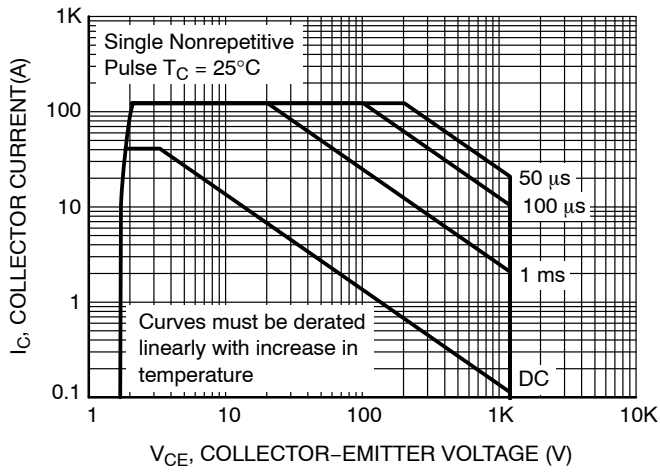


Figure 17. T1 & T2 FBSOA

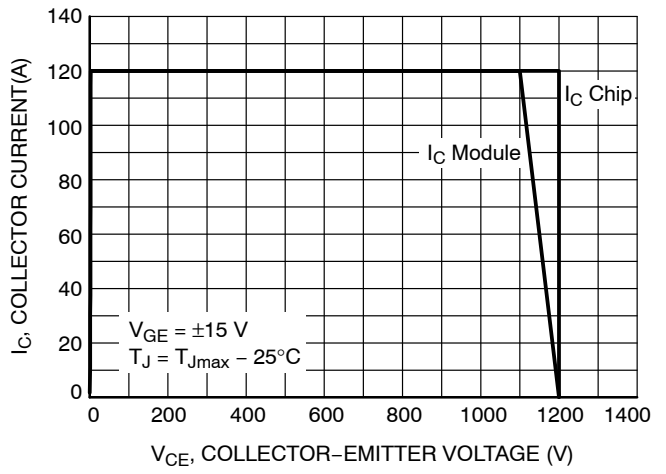


Figure 18. T1 & T2 RBSOA



# NXH80B120H2Q0

## TYPICAL CHARACTERISTICS – IGBT Protection Diode and Bypass Diode

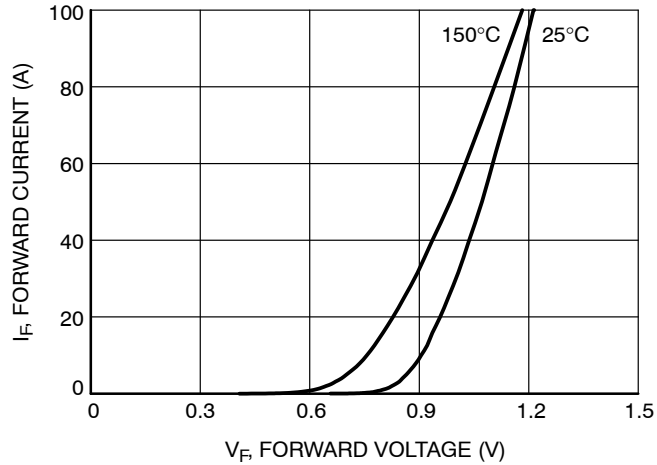


Figure 19. Diode Forward Characteristic

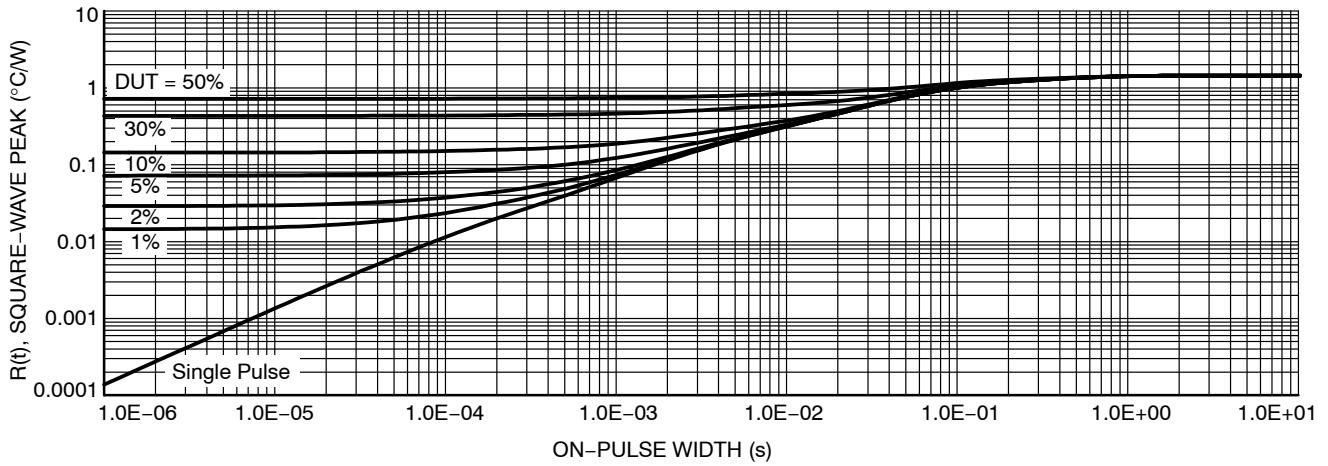


Figure 20. Diode Transient Thermal Impedance Bypass Diode / IGBT Protection Diode

## TYPICAL CHARACTERISTICS – Thermistor

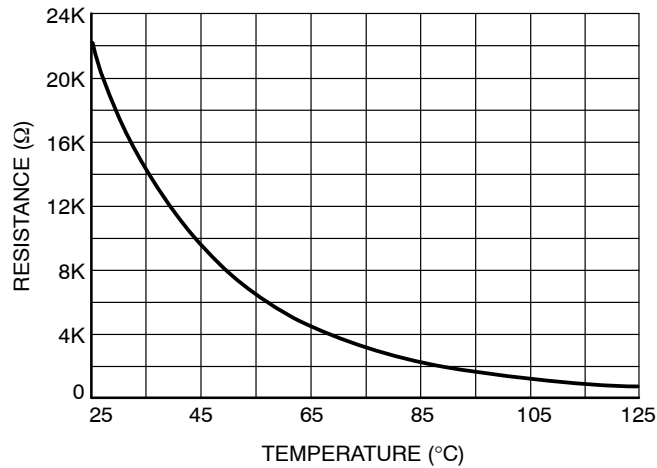
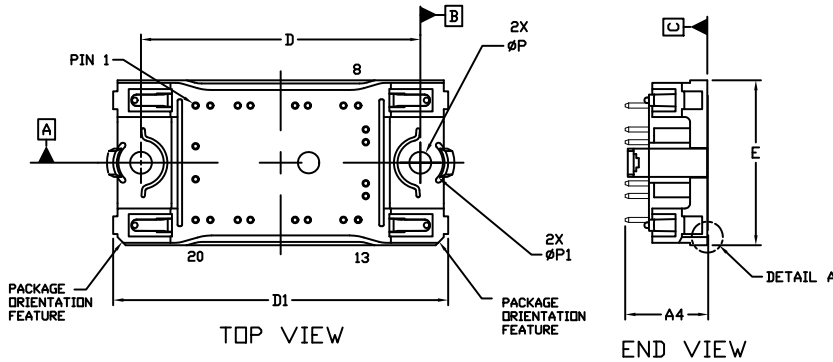


Figure 21. Thermistor Characteristic

# NXH80B120H2Q0

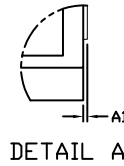
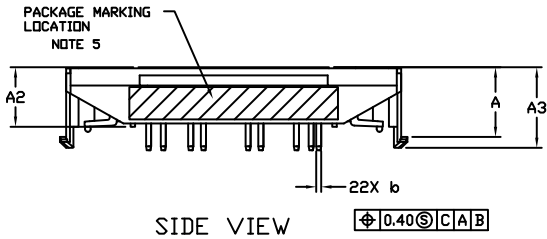
## PACKAGE DIMENSIONS

### PIM22, 55x32.5 / Q0BOOST CASE 180AJ ISSUE A



#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION *b* APPLIES TO THE PLATED TERMINALS AND IS MEASURED BETWEEN 1.00 AND 3.00 FROM THE TERMINAL TIP.
4. POSITION OF THE CENTER OF THE TERMINALS IS DETERMINED FROM DATUM B THE CENTER OF DIMENSION D, X DIRECTION, AND FROM DATUM A, Y DIRECTION. POSITIONAL TOLERANCE, AS NOTED IN DRAWING, APPLIES TO EACH TERMINAL IN BOTH DIRECTIONS.
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES.



DIM	MILLIMETERS	
	MIN.	NOM.
A	13.50	13.90
A1	0.10	0.30
A2	11.50	11.90
A3	15.65	16.05
A4	16.35	REF
<i>b</i>	0.95	1.05
D	54.80	55.20
D1	65.60	66.20
E	32.20	32.80
P	4.20	4.40
P1	8.90	9.10

#### NOTE 4

PIN	PIN POSITION		PIN	PIN POSITION	
	X	Y		X	Y
1	-16.75	11.25	12	16.75	-6.55
2	-13.85	11.25	13	15.25	-11.25
3	-8.45	11.25	14	12.35	-11.25
4	-5.95	11.25	15	5.35	-11.25
5	2.85	11.25	16	2.85	-11.25
6	5.35	11.25	17	-5.95	-11.25
7	12.35	11.25	18	-8.45	-11.25
8	15.25	11.25	19	-13.85	-11.25
9	16.75	6.55	20	-16.75	-11.25
10	16.75	4.05	21	-16.75	-3.25
11	16.75	-4.05	22	-16.75	3.25

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Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

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